Review* of Metallic Resists for EUV

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- I. Metal-Oxo Films (OSU/Inpria)
- II. HfOx and ZrOx Nanoparticles (Cornell)
- III. Molecular Organometallic Resists for EUV (MORE) (SUNY Poly and New Paltz)
 - A. Tin Oxo Clusters (Cardineau)
 - B. Tin Carboxylates (Del Re)
 - C. Transition Metal Oxalates (Freedman)
 - D. Positive-Tone Palladium (Sortland)
 - E. High-Speed Main-Group Olefins (Passarelli)
- **IV. Acknowledgements**

*For 2nd Edition:



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Optical Density Map of the Elements



I. Metal-Oxo Films (OSU/Inpria)

First Publication of EUV Results. BMET SPIE 2010



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Naulleau & Anderson SPIE 2010 76361J1

I. Metal-Oxo Films (OSU/Inpria) Published Photoreactivity

The key to the photoreactivity of the HafSOx resists appears to be controlling the dehydration reaction (eq 1) which crosslinks and thereby reduces the solubility of these metal oxo-films. Dehydration is prevented by binding peroxide to Hf. Fortunately, the metal peroxide decomposition can be induced by highenergy light or electrons (eq 2) thereby creating metal hydroxides that can condense and become insoluble.

In brief, the metal peroxides allow the resists to dissolve in the unexposed regions and upon photolysis the metal peroxides become metal hydroxides and condense to become insoluble features of the negative-tone resists.

 $Hf - OH + HO - Hf \longrightarrow Hf - O - Hf + H_2O$ (1)

$$Hf \begin{pmatrix} O \\ I \end{pmatrix} + \begin{pmatrix} O \\ I \end{pmatrix} Hf \xrightarrow{hv, e^{-}} Hf \begin{pmatrix} O-H \\ O-H \end{pmatrix} + \begin{pmatrix} H-O \\ H-O \end{pmatrix} Hf (2)$$

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Amador & Keszler SPIE 2014 90511A

I. Metal-Oxo Films (OSU/Inpria) Imaging at PSI (2014)



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Ekinci & Vockenhuber SPIE 2014 904804

I. Metal-Oxo Films (OSU/Inpria) Imaging at PSI (2014)

HP=12 nm

HP=8 nm



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Ekinci & Vockenhuber SPIE 2014 904804

II. HfOx and ZrOx Nanoparticles (Cornell)

Many versions of these resists were prepared using methacrylate as a ligand and formulated with either photoacid generators or free-radical initiators, suggesting that the negative-tone imaging mechanisms might involve free-radical crosslinking.

ON

- Ph₂S etc

TPSONF PAG

hy or 2º et

However, careful studies revealed that the negative-tone solubility switches do not involve free-radical crosslinking, but instead involves a ligand exchange mechanism that can proceed without PAGs or with the assistance of PAGs.



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II. HfOx and ZrOx Nanoparticles (Cornell)

These nanoparticle resists are capable of good EUV patterning capability at extremely fast photospeeds. 20 and 30 nm isolated lines were printed using doses of 2.4 and 1.6 mJ/cm². Although the LER values of these resists are modest (5-7 nm), the LER is not too poor considering that the resists are extremely sensitive and are composed of nanoparticles that are 1-2 nm in diameter.



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Jiang & Ober JPST 2014 27, 663

III. MORE: A. Tin Oxo Clusters (Cardineau)





 $[(PhSn)_{12}O_{14}(OH)_6]Cl_2$

Dose: 350 mJ/cm²

Resolution: 18 nm



The resist sensitivity shows good correlation with anion size.

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Cardineau & Brainard MicElec 127 (2014) 44





II. MORE: B. Low LER Tin Resists (Del Re) LER Does Not Follow Z Parameter





III. MORE: C. Transition Metal Oxalates (Freedman)







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Freedman & Brainard SPIE 2014

III. MORE: C. Transition Metal Oxalates (Freedman)



III. MORE: D. Positive-Tone Palladium Resists (Sortland)



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Sortland & Brainard JM3 2015 043511

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Excellent sensitivity at modest resolution.



Proposed mechanism is based on photo-initiated free radical polymerization.





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Passarelli & Brainard JM3 2015 043503

Unexpected Result: Changing Sb-R bond did not dramatically affect sensitivity.





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Sensitivity Hypothesis: The ratio of polymerizable olefins to space filling R groups is the largest contributor to sensitivity characteristics of antimony acrylate resists.

$$POL = \frac{\# of Polymerizable Olefins}{\# of Atoms (Excluding Hydrogen)} \times 100\%$$

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